Jean-Marc Jancu

List of Publications by Year in descending order

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IEAN-MARC IANCU

#	Article	IF	CITATIONS
1	Assessment of GaPSb/Si tandem material association properties for photoelectrochemical cells. Solar Energy Materials and Solar Cells, 2021, 221, 110888.	6.2	4
2	Anharmonicity and Disorder in the Black Phases of Cesium Lead Iodide Used for Stable Inorganic Perovskite Solar Cells. ACS Nano, 2018, 12, 3477-3486.	14.6	546
3	Anharmonicity and Disorder in the Black Phases of CsPbI3 used for Stable Inorganic Perovskite Solar Cells. , 2018, , .		1
4	Symmetry-Based Tight Binding Modeling of Halide Perovskite Semiconductors. Journal of Physical Chemistry Letters, 2016, 7, 3833-3840.	4.6	57
5	Theoretical insights into hybrid perovskites for photovoltaic applications. , 2016, , .		6
6	Density Functional Theory Simulations of Semiconductors for Photovoltaic Applications: Hybrid Organic-Inorganic Perovskites and III/V Heterostructures. International Journal of Photoenergy, 2014, 2014, 1-11.	2.5	23
7	Electronic properties of 2D and 3D hybrid organic/inorganic perovskites for optoelectronic and photovoltaic applications. Optical and Quantum Electronics, 2014, 46, 1225-1232.	3.3	60
8	DFT and <i>k</i> · <i>p</i> modelling of the phase transitions of lead and tin halide perovskites for photovoltaic cells. Physica Status Solidi - Rapid Research Letters, 2014, 8, 31-35.	2.4	177
9	Importance of Spin–Orbit Coupling in Hybrid Organic/Inorganic Perovskites for Photovoltaic Applications. Journal of Physical Chemistry Letters, 2013, 4, 2999-3005.	4.6	1,021
10	Theoretical and experimental studies of (In,Ga)As/GaP quantum dots. Nanoscale Research Letters, 2012, 7, 643.	5.7	4
11	Large intrinsic birefringence in zinc-blende based artificial semiconductors. Comptes Rendus Physique, 2007, 8, 1174-1183.	0.9	1
12	Normal-incidence intersubband absorption in AlGaSb quantum wells. Journal of Applied Physics, 2002, 92, 641-643.	2.5	5
13	Boundary conditions in multibandkâ‹pmodels: A tight-binding test. Physical Review B, 1999, 59, 9691-9694.	3.2	15
14	Empiricalspds*tight-binding calculation for cubic semiconductors: General method and material parameters. Physical Review B, 1998, 57, 6493-6507.	3.2	658
15	Evidence of electronic confinement in pseudomorphic Si/GaAs superlattices. Physical Review B, 1998, 57, R15100-R15103.	3.2	3
16	[001] strain-induced band mixing in zinc-blende semiconductors: Intravalence versus upper-conduction–valence band effects. Physical Review B, 1994, 50, 16956-16963.	3.2	14
17	Equations of state and a tight-binding model for strained layers: Application to a ZnSe-GaAs epilayer. Physical Review B, 1993, 48, 2452-2459.	3.2	17
18	Uniaxial-stress determination of the symmetry of excitons associated with the miniband dispersion in (Ga,In)As-GaAs superlattices. Physical Review B, 1992, 46, 4764-4768.	3.2	18